

N-channel TrenchMOS logic level FET Rev. 02 — 9 February 2011

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	Quick reference	data				
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	46	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	157	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	22	27	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 6}{\text{Figure } 7};$ see Figure 7	-	24	29	mΩ

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Тур

-

Max Unit

152 mJ

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Table 1.	Quick reference	datacontinued	
Symbol	Parameter	Conditions	Min
Avalanche	e ruggedness		
E _{DS(AL)S}	non-repetitive	$I_D = 46 \text{ A}; V_{sup} \le 100 \text{ V};$	-

- () -	drain-source avalanche energy	$R_{GS} = 50 \Omega; V_{GS} = 5 V;$ $T_{j(init)} = 25 °C; unclamped$				
Dynamic of	characteristics					
Q_{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 80 V; T _j = 25 °C; see <u>Figure 8</u>	-	13	-	nC

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9629-100B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

Simplified outline

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		5, (
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-15	15	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; see <u>Figure 1;</u> see <u>Figure 3</u>	-	46	А
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	-	32	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>	-	186	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	157	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	46	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	186	А
Avalanche i	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 46 \text{ A}; V_{sup} \le 100 \text{ V}; R_{GS} = 50 \Omega;$ $V_{GS} = 5 \text{ V}; T_{j(init)} = 25 \text{ °C}; \text{ unclamped}$	-	152	mJ

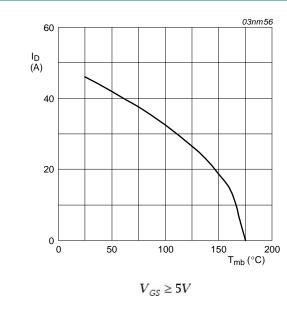


Fig 1. Normalized continuous drain current as a function of mounting base temperature

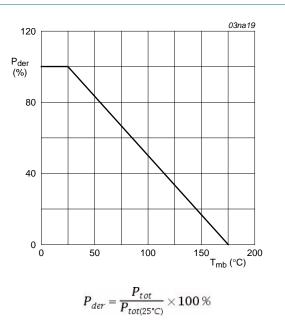


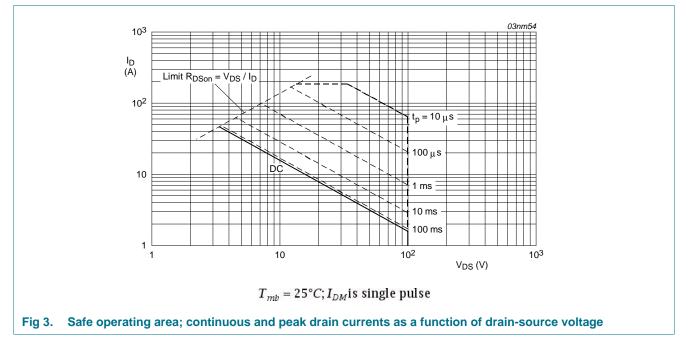
Fig 2. Normalized total power dissipation as a function of mounting base temperature

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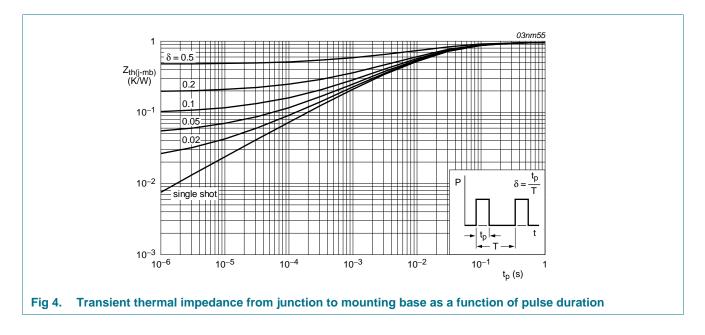
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 5</u>	1.1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 5</u>	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 5</u>	0.5	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I _{GSS}	gate leakage current	$V_{GS} = 15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V_{GS} = -15 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	R _{DSon} drain-source on-state	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	32	mΩ
resistance	resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 6</u> ; see <u>Figure 7</u>	-	-	75	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	22	27	mΩ
		$V_{GS} = 5 \text{ V}; \text{ I}_D = 25 \text{ A}; \text{ T}_j = 25 \text{ °C};$ see Figure 6; see Figure 7	-	24	29	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$	-	33	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 8</u>	-	7	-	nC
Q _{GD}	gate-drain charge		-	13	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	3270	4360	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 9</u>	-	236	283	pF
C _{rss}	reverse transfer capacitance		-	103	141	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	30	-	ns
t _r	rise time	R _{G(ext)} = 10 Ω; T _j = 25 °C	-	86	-	ns
t _{d(off)}	turn-off delay time		-	96	-	ns
t _f	fall time		-	46	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	7.5	-	nH

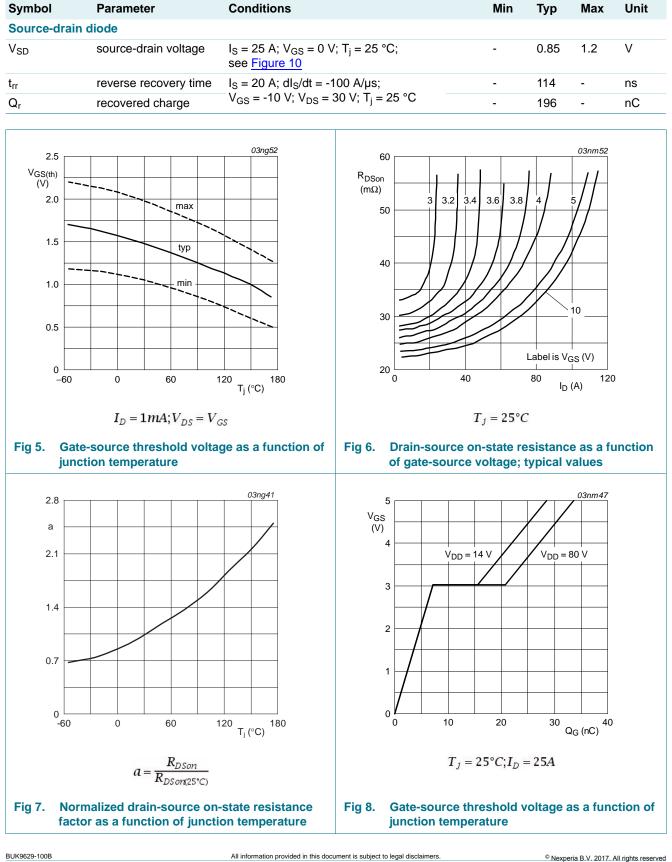
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Table 6.

Characteristics ... continued

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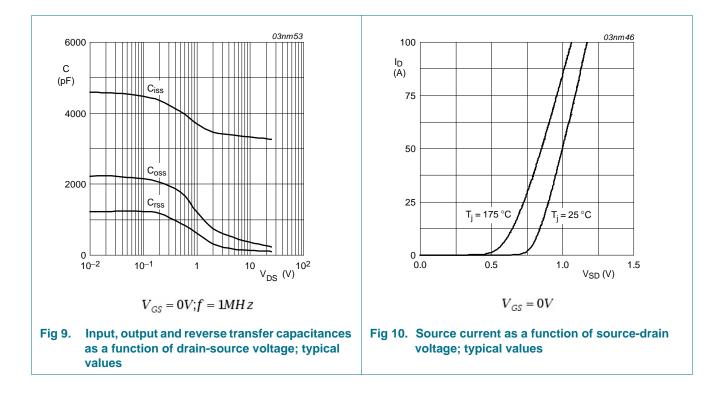


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7. Package outline

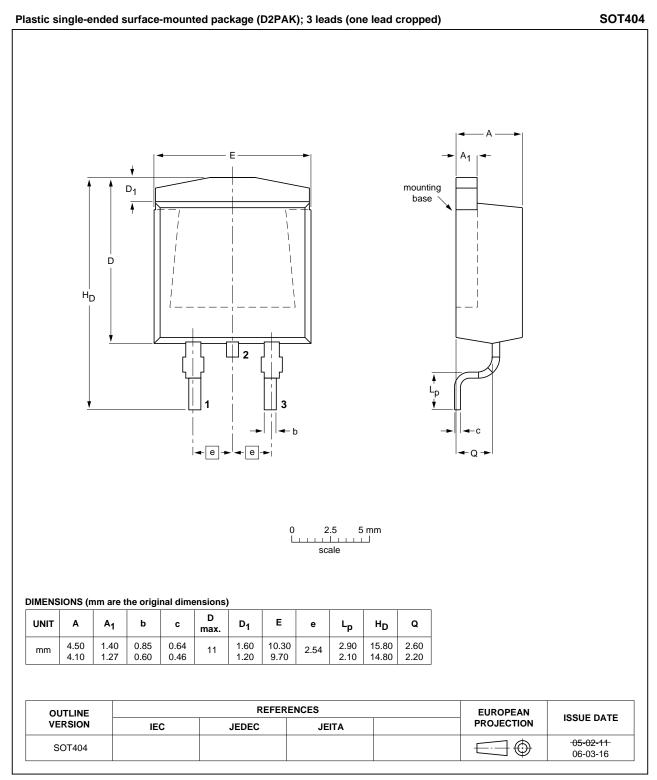


Fig 11. Package outline SOT404 (D2PAK)

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8. Revision history

tory			
Release date	Data sheet status	Change notice	Supersedes
20110209	Product data sheet	-	BUK95_9629_100B v.1
		lesigned to comply with	n the new identity guidelines
 Legal texts have 	been adapted to the new	company name wher	e appropriate.
 Type number BU 	K9629-100B separated f	rom data sheet BUK98	5_9629_100B v.1.
20030418	Product data	-	-
	20110209 • The format of this of NXP Semicon • Legal texts have • Type number BU	Release date Data sheet status 20110209 Product data sheet • The format of this data sheet has been red of NXP Semiconductors. • Legal texts have been adapted to the new • Type number BUK9629-100B separated for the new	Release date Data sheet status Change notice 20110209 Product data sheet - • The format of this data sheet has been redesigned to comply with of NXP Semiconductors. - • Legal texts have been adapted to the new company name where • Type number BUK9629-100B separated from data sheet BUK95

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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